

# P-Channel 30 V (D-S) MOSFET

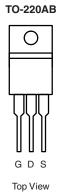
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>			
- 30	$0.013 \text{ at V}_{GS} = -10 \text{ V}$	- 80			
	0.016 at V <sub>GS</sub> = - 4.5 V	- 80			

### **FEATURES**

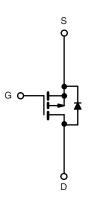
• Compliant to RoHS Directive 2002/95/EC



RoHS'







P-Channel MOSFET

Parameter	Symbol	Limit	Unit V		
Gate-Source Voltage	$V_{GS}$	± 20			
Oastings	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 80 <sup>a</sup>	•	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 125 °C		- 65		
Pulsed Drain Current	I <sub>DM</sub>	- 240	Α		
Avalanche Current	I <sub>AR</sub>	- 60			
Repetitive Avalanche Energy <sup>b</sup>	L = 0.1 mH	E <sub>AR</sub>	180	mJ	
Device Diseisettes	T <sub>C</sub> = 25 °C (TO-220AB and TO-263)	В	187 <sup>d</sup>	W	
Power Dissipation	T <sub>A</sub> = 25 °C (TO-263) <sup>c</sup>	$P_{D}$	3.75		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>sta</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Limit	Unit		
Junction-to-Ambient	PCB Mount (TO-263) <sup>c</sup>	В	40			
Junction-to-Ambient	Free Air (TO-220AB)	R <sub>thJA</sub>	62.5	°C/W		
Junction-to-Case	•	$R_{thJC}$	0.8	1		

### Notes:

- a. Package limited.
- b. Duty cycle  $\leq$  1 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. See SOA curve for voltage derating.

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 1		- 3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50	μΑ	
		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 120			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.0055	0.013	Ω	
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C			0.020		
Dialit-Source Oit-State nesistance	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}, T_J = 175 ^{\circ}\text{C}$			0.033		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.008	0.016		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 75 A	20			S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			9000		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		1565			
Reversen Transfer Capacitance	C <sub>rss</sub>			715			
Total Gate Charge <sup>c</sup>	$Q_g$			160	240	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -75 \text{ A}$		32			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			30			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			25	40	ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 0.2 \Omega$		225	360		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -75 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		150	240		
Fall Time <sup>c</sup>	t <sub>f</sub>	]		210	340		
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>	(T <sub>C</sub> = 25 °C)					
Continuous Current	I <sub>S</sub>				- 75	Δ.	
Pulsed Current	I <sub>SM</sub>				- 240	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = -75 A, V <sub>GS</sub> = 0 V		- 1.2	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			55	100	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 75 A, dl/dt = 100 A/μs		2.5	5	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	1		0.07	0.25	μС	

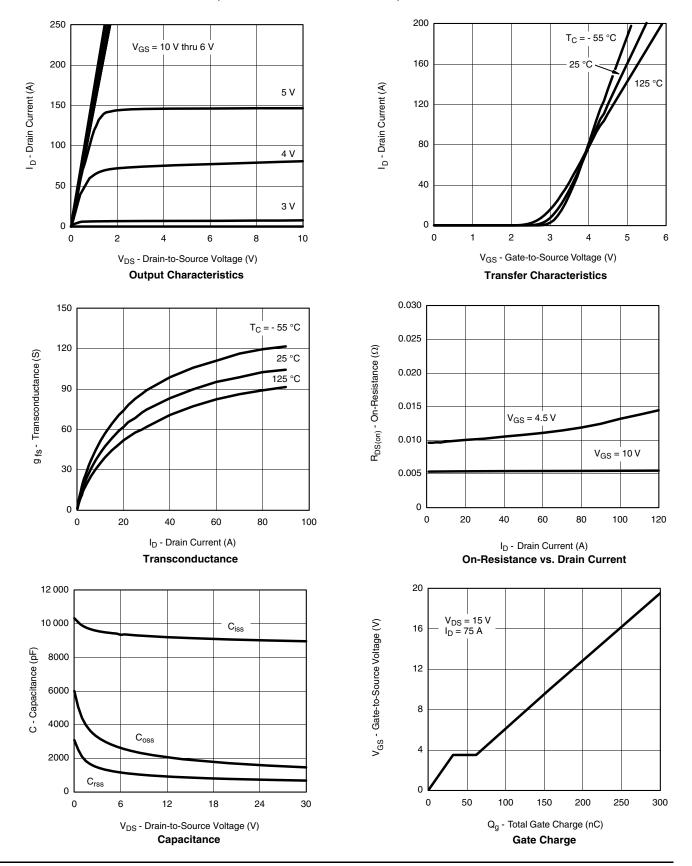
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

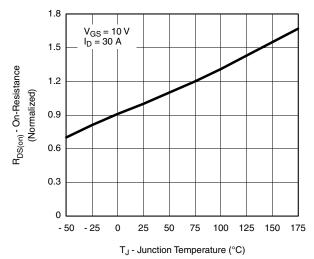


### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

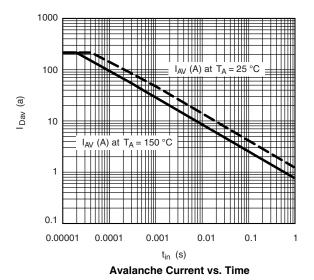




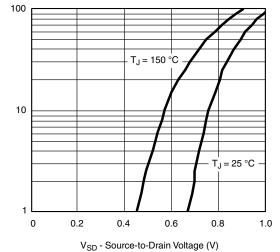
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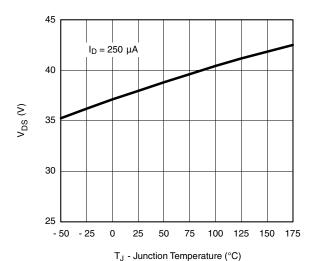
On-Resistance vs. Junction Temperature



I<sub>S</sub> - Source Current (A)



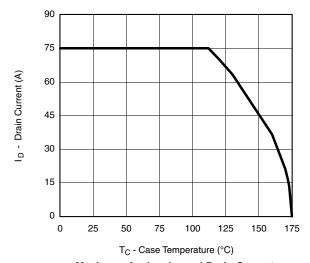
Source-Drain Diode Forward Voltage



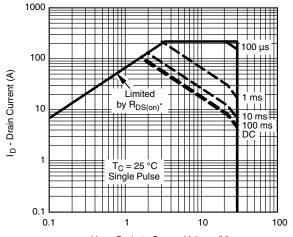
Drain Source Breakdown vs. Junction Temperature



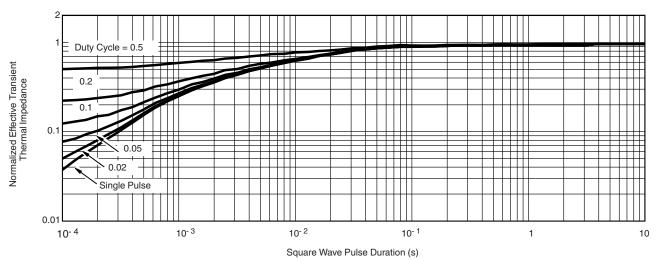
#### **THERMAL RATINGS**



Maximum Avalanche and Drain Current vs. Case Temperature



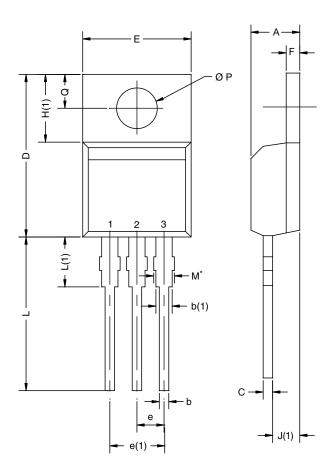
$$\begin{split} V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ \text{* $V_{GS}$} \text{ minimum $V_{GS}$ at which $R_{DS(on)}$ is specified} \\ \textbf{Safe Operating Area} \end{split}$$



Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-220AB**



	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

#### Notes

 $<sup>^{*}</sup>$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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